## Nch 20V 10A Middle Power MOSFET

V <sub>DSS</sub>	20V
R <sub>DS(on)</sub> (Max.)	12mΩ
I <sub>D</sub>	±10A
P <sub>D</sub>	2.0W

## Features

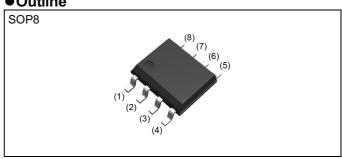
- 1) Low on resistance.
- 2) High Power small mold Package (SOP8).
- 3) Pb-free lead plating; RoHS compliant.

# Application

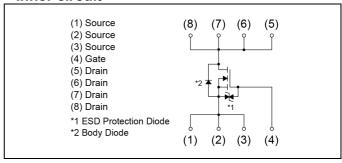
Switching

	Taping of	Taping code  Marking					
	Marking						
● Absolute maximum ratings (T <sub>a</sub> = 25°C)							
Parameter	Symbol	Value	Unit				
Drain - Source voltage	V <sub>DSS</sub>	20	V				
Continuous drain current	I <sub>D</sub>	±10	А				
Pulsed drain current	I <sub>D,pulse</sub> *1	±36	А				
Gate - Source voltage	$V_{GSS}$	±10	V				
Power dissipation	P <sub>D</sub> *2	2.0	W				
Junction temperature	T <sub>j</sub>	150	°C				

#### Outline



### ●Inner circuit



Packaging specifications

	ing opcomouncing	
Туре	Packing	Embossed Tape
	Reel size (mm)	330
	Tape width (mm)	12
	Basic ordering unit (pcs)	2500
	Taping code	ТВ
	Marking	RUS100N02

-55 to +150

Range of storage temperature

°C

 $T_{stg}$ 

### ●Thermal resistance

Downwater	Cymbol	Values			l limit
Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance, junction - ambient	R <sub>thJA</sub> *2	-	62.5	1	°C/W

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

Davamatav	Cymahal	Conditions	Values			l loit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain - Source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA	20	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}}$	I <sub>D</sub> = 1mA referenced to 25°C	-	18.7	-	mV/°C
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V	-	-	1	μΑ
Gate - Source leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$	-	-	±10	μA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	0.3	-	1.0	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_{j}}$	I <sub>D</sub> = 1mA referenced to 25°C	-	2.5	-	mV/°C
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 10A	-	8	12	
Static drain - source	D *3	V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 10A	-	9	13	mΩ
on - state resistance	R <sub>DS(on)</sub> *3	$V_{GS} = 1.8V, I_D = 5A$	-	11	16	11122
		$V_{GS} = 1.5V, I_D = 2.5A$	1	13	19	
Forward Transfer Admittance	Y <sub>fs</sub>  *3	V <sub>DS</sub> = 10V, I <sub>D</sub> = 10A	15	-	-	S

<sup>\*1</sup> Pw  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

<sup>\*2</sup> Mounted on a ceramic boad

<sup>\*3</sup> Pulsed

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

Doromotor	Currente ed	Canditions	Values			l leit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	2250	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 10V	-	550	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	280	-	
Turn - on delay time	$t_{d(on)}^{*3}$	$V_{DD} \simeq 10V, V_{GS} = 4.5V$	-	25	-	
Rise time	t <sub>r</sub> *3	I <sub>D</sub> = 5A	-	65	-	no
Turn - off delay time	t <sub>d(off)</sub> *3	$R_L \simeq 2\Omega$	-	125	-	ns
Fall time	<b>t</b> <sub>f</sub> *3	$R_G = 10\Omega$	-	125	-	

## ● Gate charge characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol Conditions -	Canditions	Values			Unit
		Min.	Тур.	Max.	Offic	
Total gate charge	Q <sub>g</sub> *3	V <sub>DD</sub> ≃ 10V,	1	24	1	
Gate - Source charge	Q <sub>gs</sub> *3	I <sub>D</sub> = 10A,	-	3.2	-	nC
Gate - Drain charge	Q <sub>gd</sub> *3	V <sub>GS</sub> = 4.5V	-	6.4	-	

# ● Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol Conditions		Min.	Тур.	Max.	Offic
Body diode continuous forward current	I <sub>S</sub>	⊤ <sub>a</sub> = 25°C	-	1	1.6	А
Body diode pulse current	I <sub>SP</sub> *1	1 <sub>a</sub> - 25 C	-	-	36	Α
Forward voltage	$V_{SD}^{*3}$	$V_{GS} = 0V, I_{S} = 10A$	-	1	1.2	V

#### Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

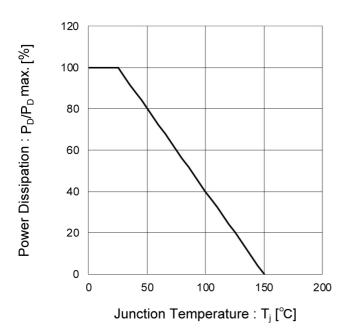
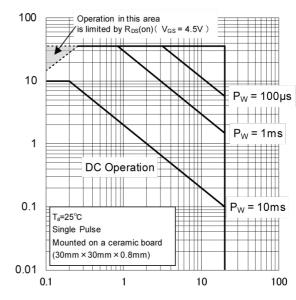


Fig.2 Maximum Safe Operating Area



Drain Current : I<sub>D</sub> [A]

Drain - Source Voltage: V<sub>DS</sub>[V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

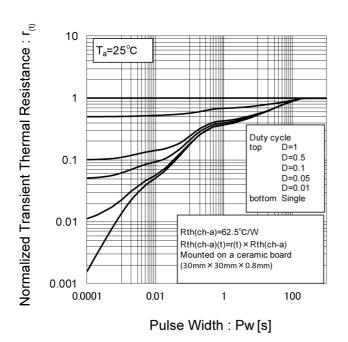
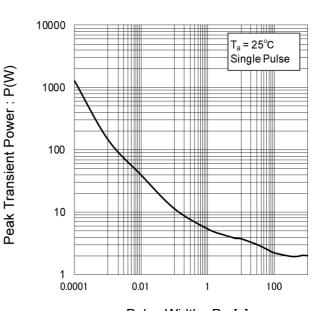


Fig.4 Single Pulse Maximum Power dissipation



Pulse Width : Pw [s]

Drain Current : I<sub>D</sub> [A]

Drain-Source Breakdown Voltage: V<sub>(BR)DSS</sub> [V]

#### Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

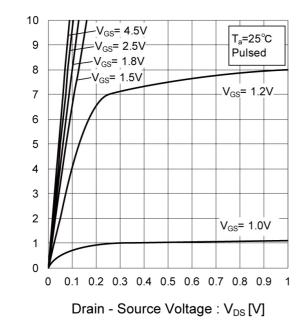


Fig.6 Typical Output Characteristics(II)

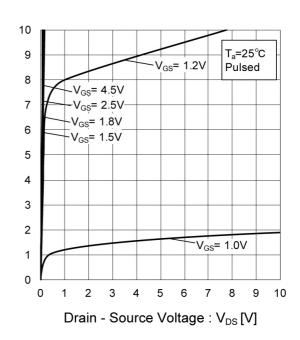


Fig.7 Breakdown Voltage vs. Junction Temperature

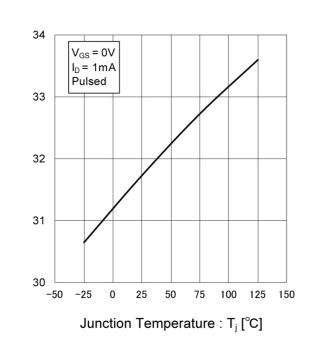
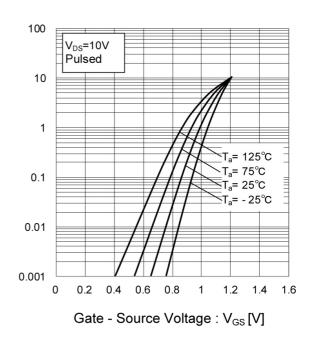


Fig.8 Typical Transfer Characteristics



Drain Current : I<sub>D</sub> [A]

Drain Current : I<sub>D</sub> [A]

#### • Electrical characteristic curves

Fig.9 Gate Threshold Voltage vs. Junction Temperature

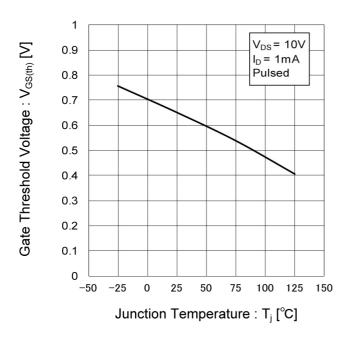


Fig.10 Tranceconductance vs. Drain Current

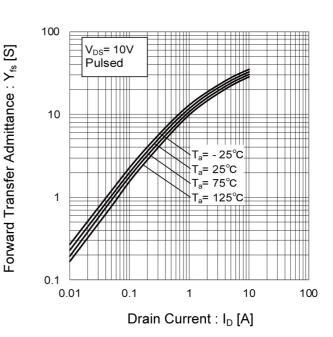


Fig.11 Drain Current Derating Curve

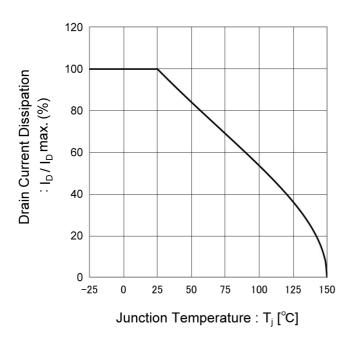
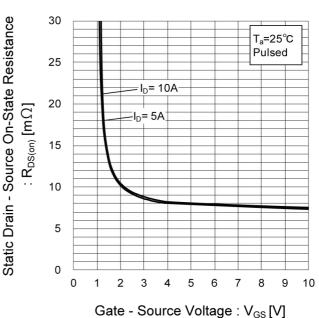


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



#### • Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

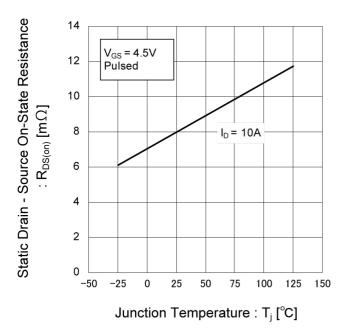


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

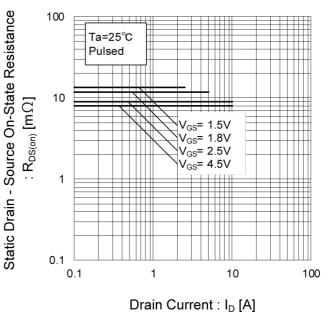


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

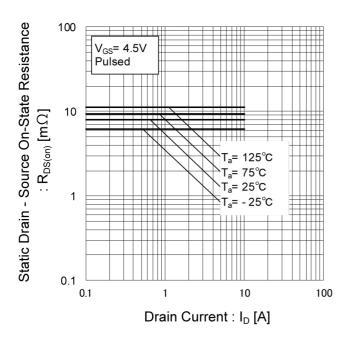
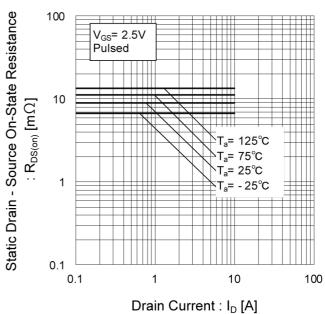


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)



#### Electrical characteristic curves

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)

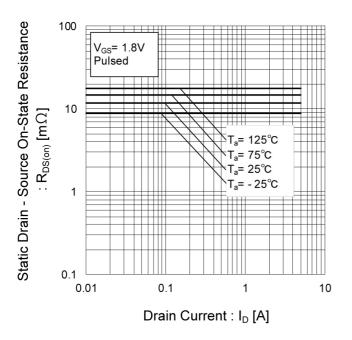


Fig.18 Static Drain - Source On - State Resistance vs. Drain Current(V)

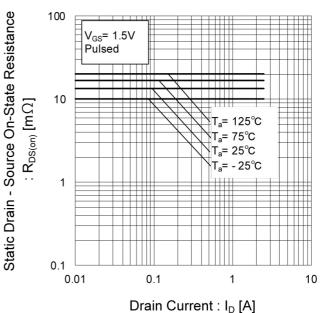
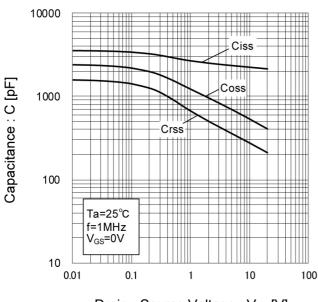
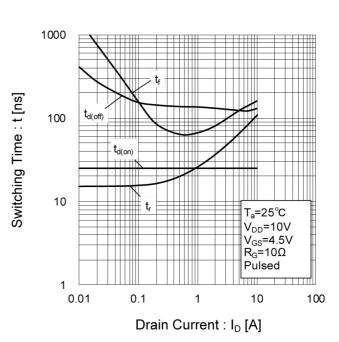


Fig.19 Typical Capacitance vs. Drain -Source Voltage



Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.20 Switching Characteristics



### • Electrical characteristic curves

Fig.21 Dynamic Input Characteristics

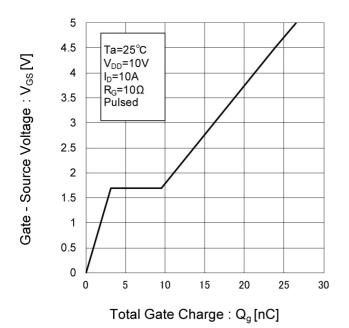
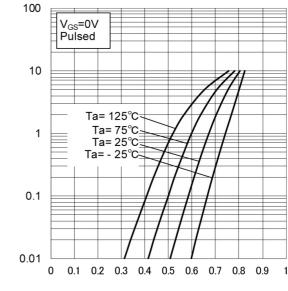


Fig.22 Source Current vs. Source Drain Voltage



Source Current : Is [A]

#### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

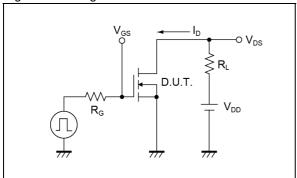


Fig.2-1 Gate Charge Measurement Circuit

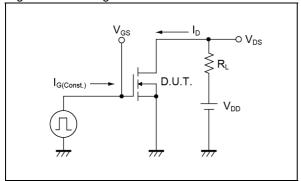


Fig.1-2 Switching Waveforms

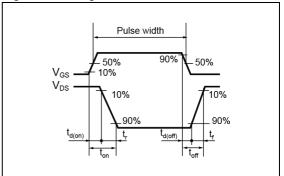
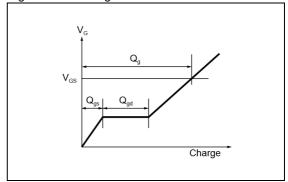
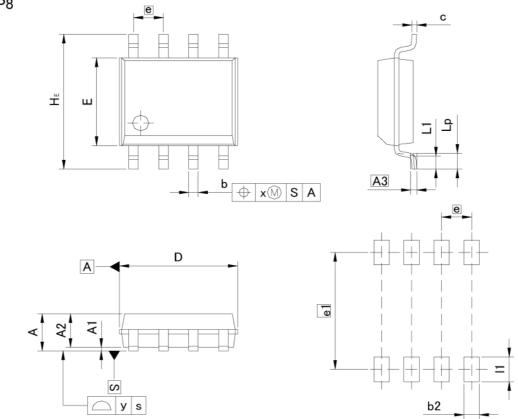


Fig.2-2 Gate Charge Waveform



### Dimensions

SOP8



Pattern of terminal position areas [Not a pattern of soldering pads]

DIM	MILIM	MILIMETERS INCHES			
DIM	MIN	MAX	MIN	MAX	
Α	-	1.75	-	0.069	
A1	0.	15	0.0	06	
A2	1.40	1.60	0.055	0.063	
A3	0.:	25	0.0	10	
b	0.30	0.50	0.012	0.020	
С	0.10	0.30	0.004	0.012	
D	4.80	5.20	0.189	0.205	
E	3.75	4.05	0.148	0.159	
е	1.3	27	0.050		
HE	5.70	6.30	0.224	0.248	
L1	0.50	0.70	0.020	0.028	
Lp	0.65	0.85	0.026	0.033	
х	0.	15	0.006		
У	0.	10	0.004		

DIM	MILIMETERS		INC	HES
DIM	MIN	MAX MIN		MAX
b2	- 0	0.65	- 0.026	
e1	5.	15	0.203	
11	<del>-</del> ->	1.15	-	0.045

Dimension in mm/inches



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